

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	373	(low near temperature) near4 ("gate oxide" or "gate dielectric" or "gate insulating")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:52
L2	153	1 and ((@ad<"19981021") or (@rlad<"19981021"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:52
L3	19953	(substrate or wafer) near8 (low near temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:52
L4	359	3 same ("gate oxide" or "gate dielectric" or "gate insulating")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:52
L5	187	4 and ((@ad<"19981021") or (@rlad<"19981021"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:53
L6	151	5 not 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 10:10
L7	2	("20040084710").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/27 10:10